Zibo Seno Electronic Engineering Co., Ltd.



SR220 – SR2200 🐯

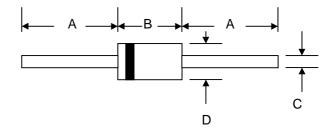
2.0A SCHOTTKY BARRIER DIODE

Features

- Schottky Barrier Chip
- Guard Ring Die Construction for Transient Protection
- High Current Capability
- Low Power Loss, High Efficiency
- High Surge Current Capability
- For Use in Low Voltage, High Frequency Inverters, Free Wheeling, and Polarity Protection Applications

Mechanical Data

- Case: DO-15, Molded Plastic
- Terminals: Plated Leads Solderable per MIL-STD-202, Method 208
- Polarity: Cathode Band
- Weight: 0.40 grams (approx.)
- Mounting Position: Any
- Marking: Type Number
- Lead Free: For RoHS / Lead Free Version



DO-15								
Dim	Min	Max						
Α	24.5	—						
В	5.50	7.62						
С	0.60	0.80						
D	2.60	3.60						
All Dimensions in mm								

Maximum Ratings and Electrical Characteristics @T_A=25°C unless otherwise specified

Single Phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

Characteristic	Symbol	SR220	SR230	SR240	SR250	SR260	SR280	SR2100	SR2150	SR2200	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	Vrrm Vrwm Vr	20	30	40	50	60	80	100	150	200	V
RMS Reverse Voltage	VR(RMS)	14	21	28	35	42	56	70	105	140	V
Average Rectified Output Current $@T_L = 75^{\circ}C$	lo	2.0								А	
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine-wave superimposed on rated load (JEDEC Method)	IFSM	50								A	
Forward Voltage $@I_F = 2.0A$	Vfm	0.55 0.70 0.85 0.90				90	V				
Peak Reverse Current $@T_A = 25^{\circ}C$ At Rated DC Blocking Voltage $@T_A = 100^{\circ}C$	Iгм	0.5 20								mA	
Typical Thermal Resistance (Note 1)	R∂jl R∂ja	28 88								°C/W	
Operating Temperature Range	Tj	-65 to +125								°C	
Storage Temperature Range	Тѕтс	-65 to +150								°C	

Note: 1. Valid provided that leads are kept at ambient temperature at a distance of 9.5mm from the case. 2. Measured at 1.0 MHz and applied reverse voltage of 4.0V D.C.

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